

# **COTS 3D NAND Flash: SEE Test Results and Challenges**

**Edward Wilcox, Michael Campola, Kenneth LaBel  
NASA Goddard Space Flight Center**

# Outline



- **Present State of Flash Memory**
- **NASA GSFC Testing Status**
  - Devices Under Test
  - 3D NAND Flash Results To Date
- **COTS Flash Memory Testing Challenges**
  - Packaging, Availability, and Electrical Access
- **Future Plans**



# Acronyms

- **COTS: Commercial Off The Shelf**
- **ECC: Error-Correcting Code**
- **EDAC: Error Detection and Correction**
- **GEO: Geostationary Earth Orbit**
- **LET: Linear Energy Transfer**
- **MBU: Multiple Bit Upset**
- **MLC: Multi-level Cell**
- **NAND: Not AND (Flash Technology)**
- **NEPP: NASA Electronics and Packaging Program**
- **QLC: Quad-level Cell**
- **RBER: Raw Bit Error Rate**
- **SBU: Single Bit Upset**
- **SEE: Single Event Effects**
- **SEFI: Single Event Functional Interruption**
- **SEU: Single Event Upset**
- **SLC: Single-level Cell**
- **SSD: Solid State Drive**
- **TID: Total Ionizing Dose**
- **TLC: Triple-level Cell**
- **UBER: Uncorrected Bit Error Rate**

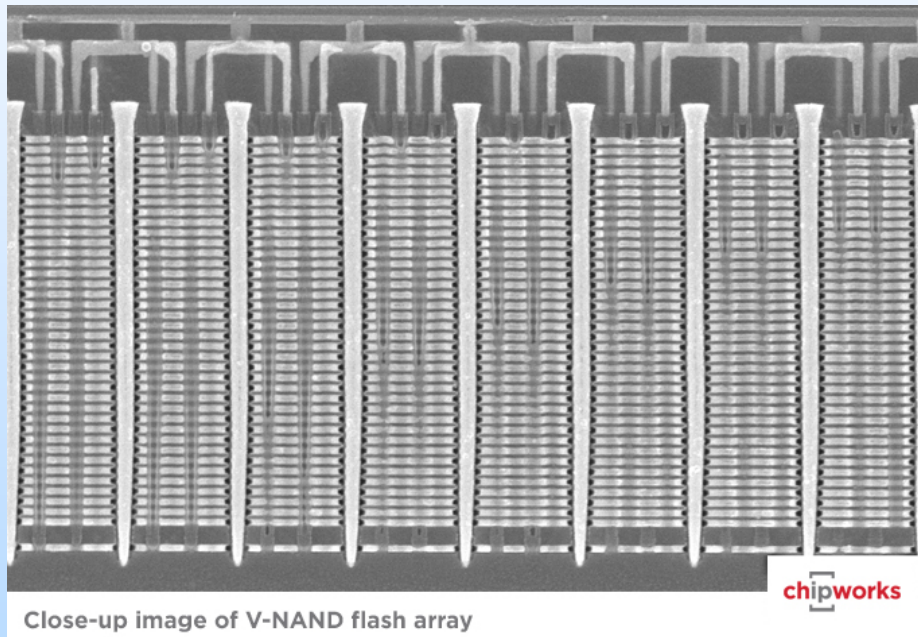
# State of Flash Memory



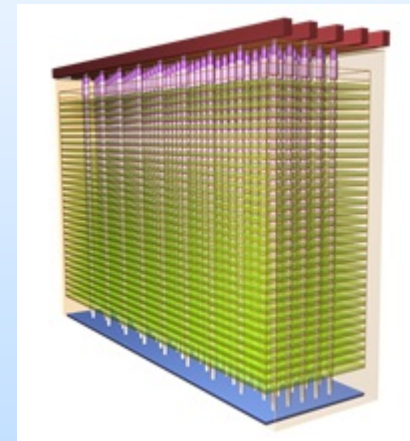
- **Limitations of 2D Highly-Scaled Flash**
- **3D Structures Maturing / Available**
  - Samsung 64-layer VNAND™
  - Toshiba / Western Digital / SanDisk 64-layer BiCS3™
  - Micron / Intel 64-layer
  - Hynix 72-layer
- **1TB SSD <\$500; 6Tb+ in a single package!**
- **Not just discrete components to worry about**
  - Integration into SoC- and SoB-type applications

# 3D NAND Structure

- Vertical flash strings, with 64 layers now common
- Not to be confused with 3D-stacking of multiple die in package



[<https://www.3dincites.com/2014/08/samsungs-3d-vnand-flash-product-spires-el-dorado/>]



[<http://www.micron.com>]

# NEPP / NASA GSFC Testing Status



- **Previous NEPP SEE testing on Hynix 3D**
  - 36 layer vs new 72-layer
  - D. Chen, NSREC 2017; TNS Jan. 2018
- **2017/2018 SEE testing on Micron MLC 3D NAND**
  - 32 Layer, floating gate technology
  - 1Tb packages with four 256Gb die
  - Limited availability / required teaming for procurement
  - Re-used simple microcontroller test setup
- **On-going SEE testing on variety of SSD modules**
  - Major manufacturers have their latest flash on SSDs
  - Easy procurement BUT limited documentation
  - No direct electrical access to memory devices

# Devices Under Test

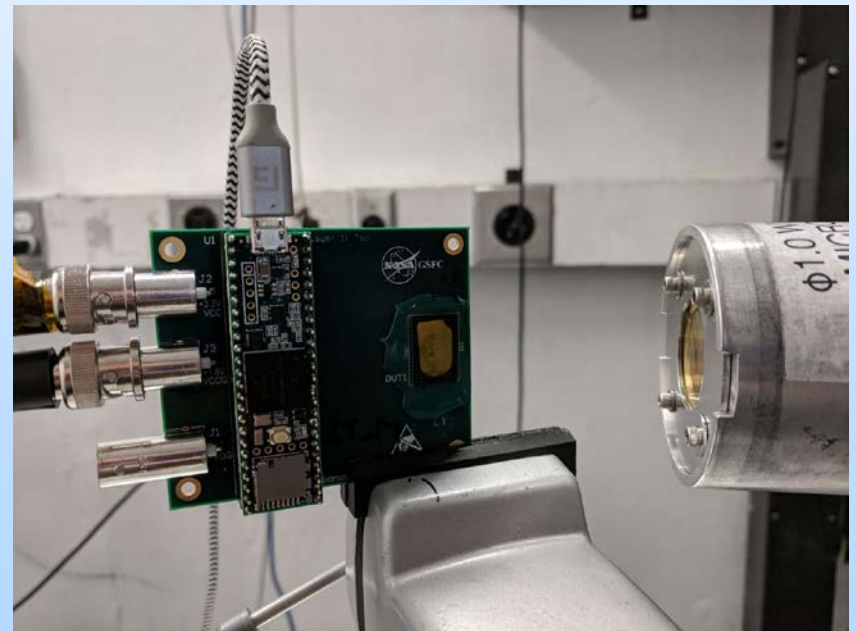


- **Micron MT29F1T08CMHBB**
  - 256Gb die; MLC; 32 layers; piece-part testing
- **Micron MT29F768G08EEHBB**
  - 384Gb die; TLC; 32 layers; Crucial MX300 SSD module
- **Intel**
  - 256Gb die; TLC; 64 layers; Intel 545 SSD module
- **Samsung**
  - TLC; 64 layers; Samsung T5 Portable SSD
- **SanDisk/Toshiba**
  - TLC; 64 layers; WD Blue 3D SSD module
  - 15nm planar TLC; WD Blue SSD module
- **Hynix H27QDG822C8R-BCG**
  - Piece-part testing; MLC; 36 layers

# Micron MT29F1T08CMHBBJ4

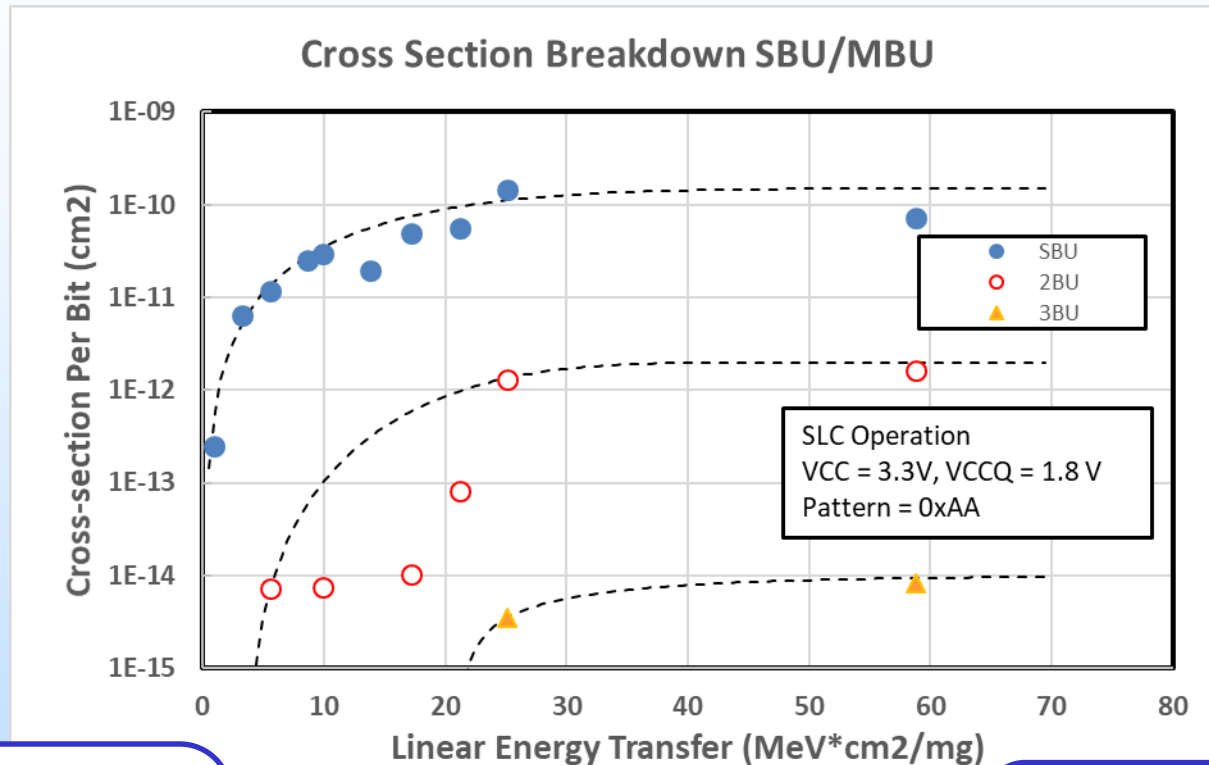


- Leveraged previous NASA test setups with Cortex-M4 microcontroller
  - Simple asynchronous interface
  - Low-level electrical access; no mapping or abstraction
  - No ECC → We can actually see bit upsets...





# Micron MT29F1T08CMHBBJ4



**In GEO, on the order of 800 upsets per Tb per year...**

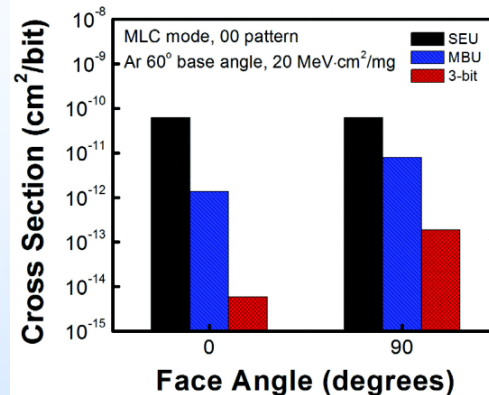
**But, MFG's ECC requirement corrects on the order of 1% error rate!**

**So, SEU are lost in the noise? Not an issue?**



# 3D NAND Angular Effects, Tilt vs. Roll

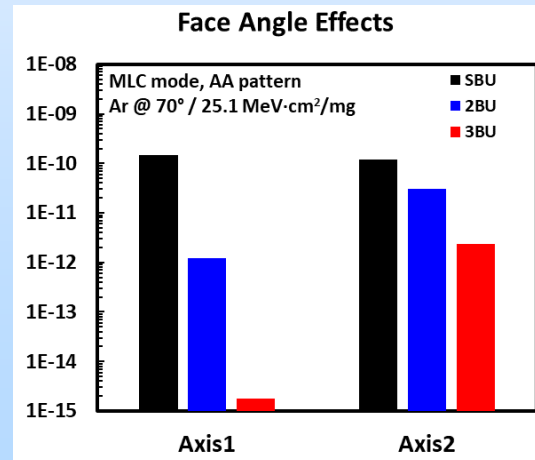
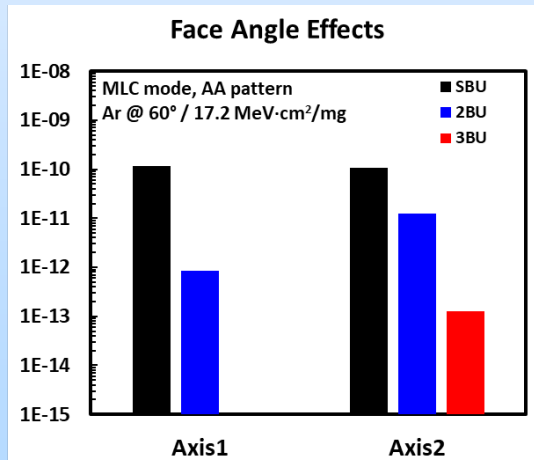
- **Dakai Chen on Hynix 36-layer MLC (TNS, 2018):**



Chen, Wilcox, et al  
[TNS, 2018]

70° angle increases MBU further

- **Micron 32-layer MLC:**



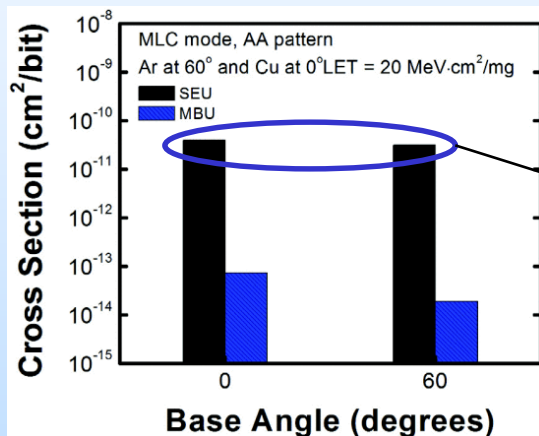
**nBU:** n upsets within a single word.  
Multiple *SBU* still possible from single particle strike

# 3D NAND Angular Effects, Constant LET



- How does “Cosine Law” apply with 3D NAND flash?

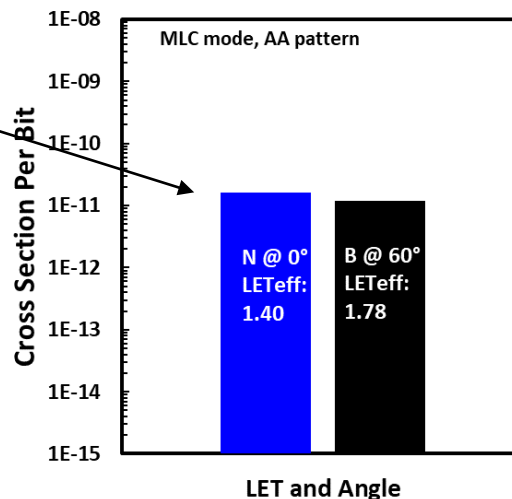
Hynix 3D:



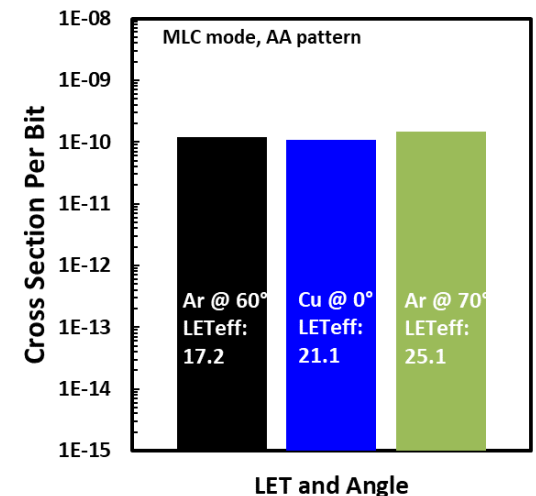
Chen, Wilcox, et al  
[TNS, 2018]

Micron 3D:

Cosine Law Effects

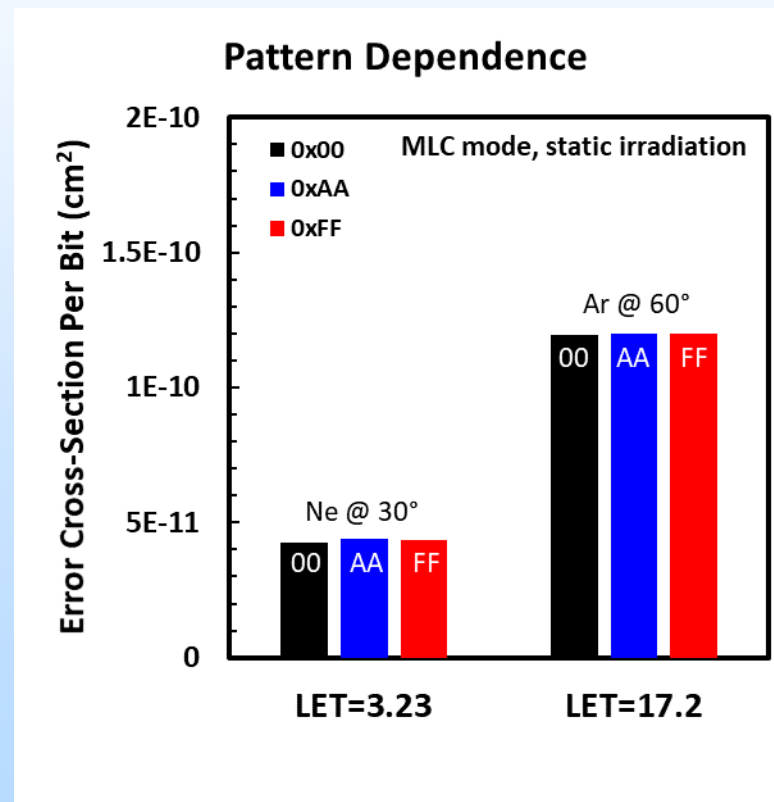


Cosine Law Effects



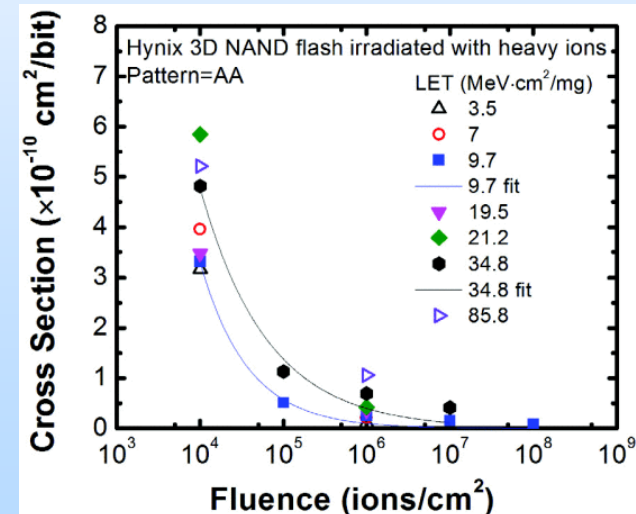
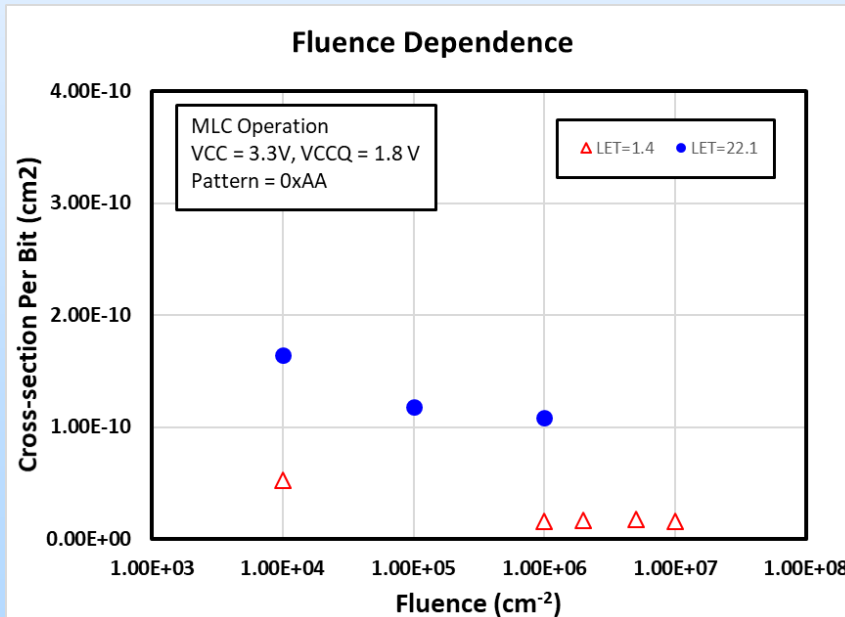
# Data Pattern Dependence

- For Micron 3D NAND, no discernable pattern dependence (0's and 1's are being mapped evenly)



# Fluence Dependence

- Programmed-cell  $V_{th}$  is a distribution – not an ideal ON or OFF
- Consider some cells “easier” to upset than others
- Reduced effect compared to previously observed Hynix 3D MLC flash.
- Relevant to understanding accelerated SEE test results!

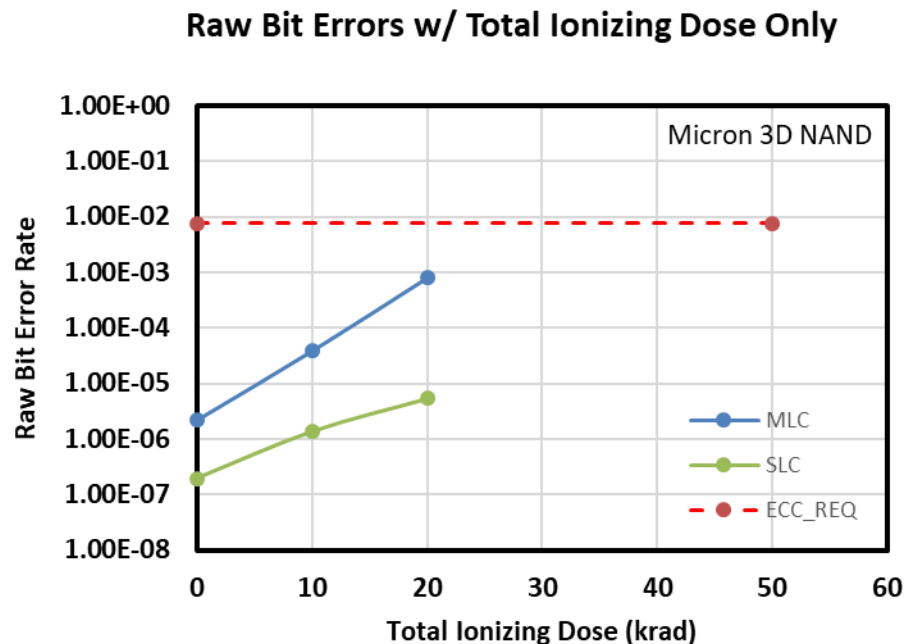


Chen, Wilcox, et al [TNS, 2018]

# TID Effects

- Let's look at adding TID into the mix
- Shifts  $V_{th}$  distribution of flash cells... just like
  - Heavy-ion particle strikes
  - Program-Erase cycles

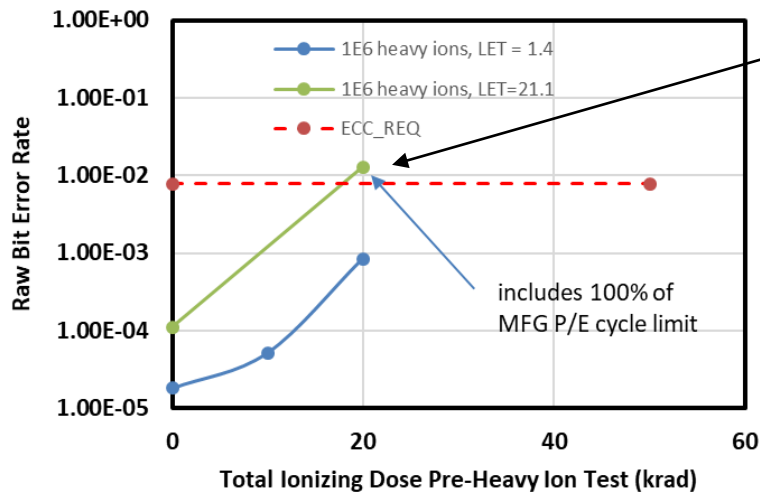
**RBER =**  
**Bit Errors/**  
**Total Bits**



# Micron Combined Effects

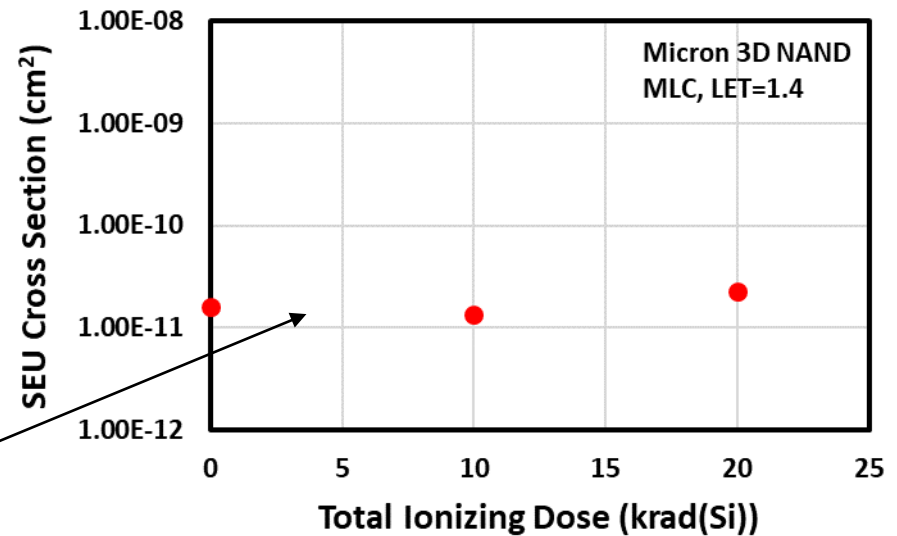
- How does TID *before* SEE affect error rate?

Combined Effect of TID, SEE, and P/E Cycles on RBER



Look out as RBER > ECC...  
but unlikely circumstances

Effect of TID on SEU Cross Section



If we subtract the TID soft errors, heavy ion-induced SEU susceptibility appears unchanged.

# SSD Test Setup



- **Solid State Hard Drives are easy to buy, easy to use, and hard to test at the bit level!**
  - Abstraction, logical address mapping, EDAC, etc
- **Number of upsets expected from SEU *low* compared to memory size and built-in error rate**
- **Can we observe general trends from manufacturer-to-manufacturer in state-of-the-art 3D NAND flash?**
- **Can TID or program/erase cycling magnify effect for easier comparison?**
- **Can we learn anything about effects of SEU on SSDs?**



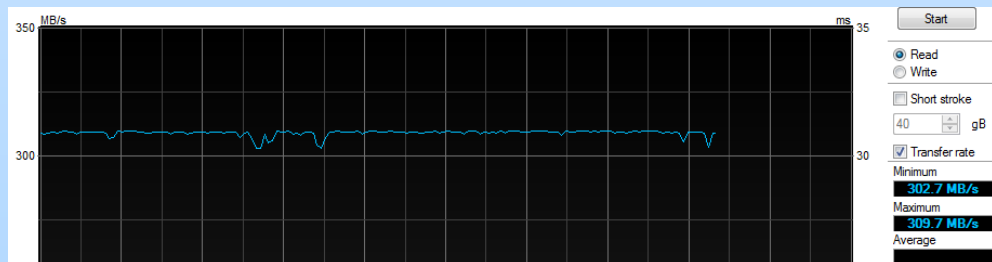
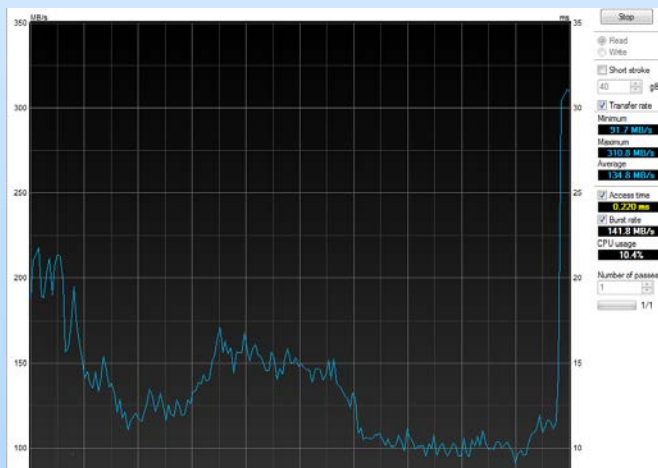
# SSD Test Results – WD Blue 3D SSD



- Irradiated to  $1 \times 10^6 \text{ cm}^{-2}$  N (LET 1.4 MeV-cm<sup>2</sup>/mg)
  - Nothing observed on tester...
- Up to  $1 \times 10^8 \text{ cm}^{-2}$ 
  - Still nothing
  - Based on Micron 3D NAND testing we'd guess on the order of .0016 upsets/bit
  - No reported uncorrectable errors



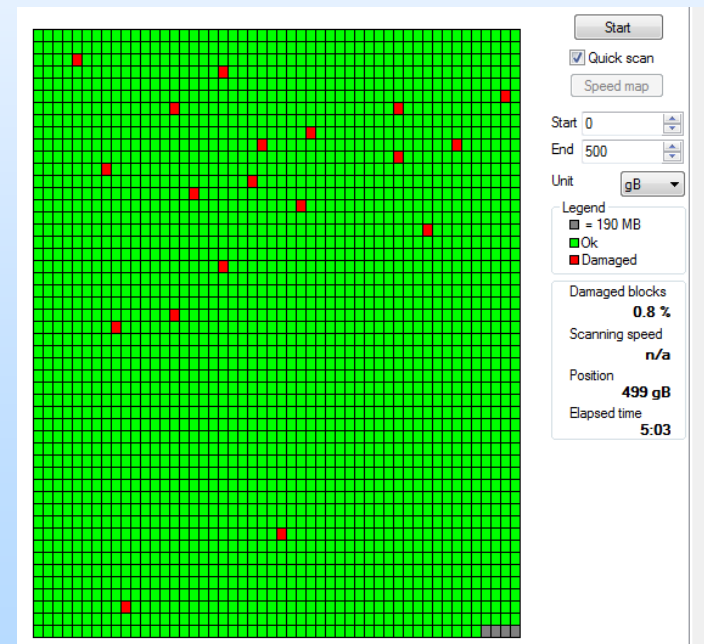
Even when errors aren't visible,  
other parametrics may suffer  
(SSD data rate lower by 50%  
after "hidden" SEUs)





# WD Blue 3D Continued

- **Pre-SEE testing: 10krad (Si) exposure**
  - No SSD errors noted following TID
- **Irradiated to  $1 \times 10^7 \text{cm}^{-2}$  Copper (LET 21.1 MeV·cm<sup>2</sup>/mg)**
  - Waited for full readback of drive... and nothing.
- **Up to  $1 \times 10^8 \text{cm}^{-2}$** 
  - Based on Micron 3D NAND MLC testing we'd guess on the order of .010 upsets/bit.
  - Errors abound (next slide)!



# WD 3D Blue SSD Data



- Nothing abnormal noted immediately after run:

(AC) Erase Fail Block Count	100	100	0	0	ok
(AD) Wear Leveling Count	100	100	0	0	ok
(AE) Unexpected Power Loss Count	100	100	0	4	ok
(B8) End To End Error Detection	100	100	0	0	ok
(BB) Uncorrectable Error Count	100	100	0	0	ok
(BC) Command Timeout	100	100	0	0	ok
(C2) Temperature	100	50	0	214748364...	ok
(C7) Interface CRC Error Count	100	100	0	0	ok

- But, after reading back drive:

(AC) Erase Fail Block Count	100	100	0	0	ok
(AD) Wear Leveling Count	100	100	0	0	ok
(AE) Unexpected Power Loss Count	100	100	0	5	ok
(B8) End To End Error Detection	100	100	0	0	ok
(BB) Uncorrectable Error Count	100	100	0	78	ok
(BC) Command Timeout	100	100	0	0	ok
(C2) Temperature	57	50	0	214750527...	ok
(C7) Interface CRC Error Count	100	100	0	0	ok

**S.M.A.R.T. attributes showed interesting data only after allowing drive controller to learn its own condition.**

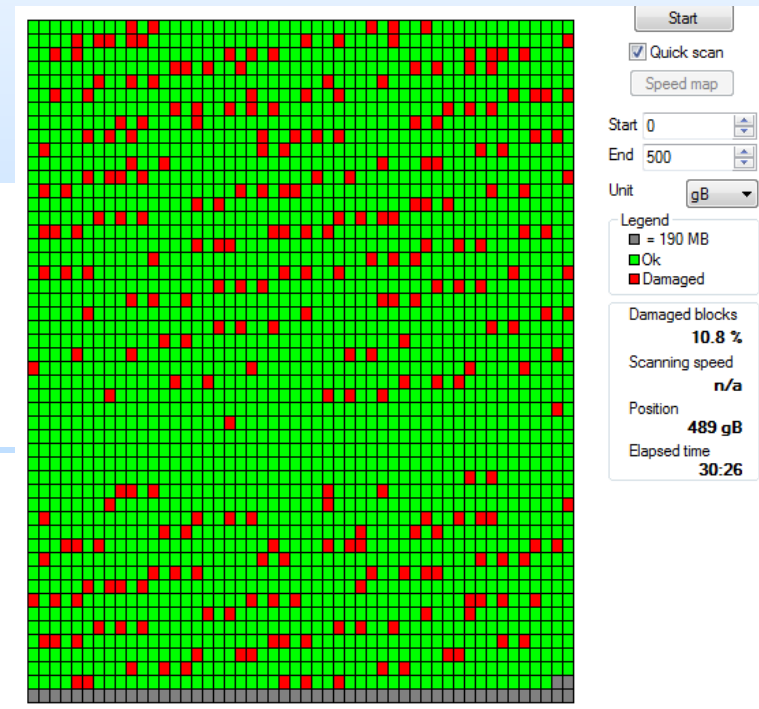
# WD 3D Blue SSD Data

- Same LET, but at 65° angle
- Pre-SEE testing: 10krad (Si) exposure
- Irradiated to  $1 \times 10^8 \text{ cm}^{-2}$  Ar @ 65° (LET 21 MeV·cm<sup>2</sup>/mg)
  - Several step irradiations with readbacks, no errors through  $5 \times 10^7 \text{ cm}^{-2}$ .
  - Big changes after final step:

(AC) Erase Fail Block Count	100	100	0	0	ok
(AD) Wear Leveling Count	100	100	0	0	ok
(AE) Unexpected Power Loss Count	100	100	0	4	ok
(B8) End To End Error Detection	100	100	0	0	ok
(BB) Uncorrectable Error Count	100	100	0	0	ok
(BC) Command Timeout	100	100	0	0	ok
(C2) Temperature	100	64	0	274877906...	ok
(C7) Interface CRC Error Count	100	100	0	0	ok

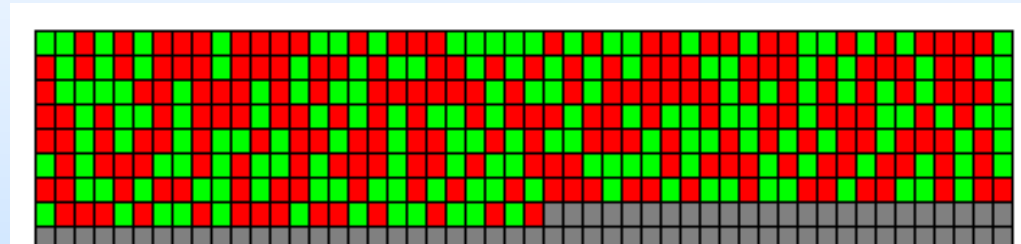
(AC) Erase Fail Block Count	100	100	0	0	ok
(AD) Wear Leveling Count	100	100	0	0	ok
(AE) Unexpected Power Loss Count	100	100	0	6	ok
(B8) End To End Error Detection	100	100	0	0	ok
(BB) Uncorrectable Error Count	100	100	0	271	ok
(BC) Command Timeout	100	100	0	0	ok
(C2) Temperature	54	64	0	274880921...	ok
(C7) Interface CRC Error Count	100	100	0	0	ok



# Other SSDs Tested



- **Intel 64-layer TLC**
  - 10 krad(Si) +  $1 \times 10^8 \text{cm}^{-2}$  @ LET 1.4:
  - All clean
  - Separate device, 0 krad,  $1 \times 10^8 \text{cm}^{-2}$  Copper (LET 21.1):

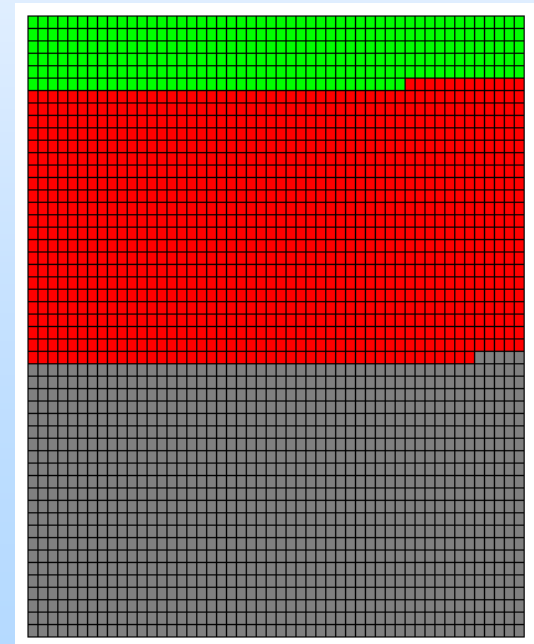


# Continued SSD Data

- **Samsung 64-layer VNAND**
  - Clean at  $1 \times 10^7 \text{cm}^{-2}$  Copper (LET 21.1 MeVcm<sup>2</sup>/mg)
  - Few errors at  $5 \times 10^7 \text{cm}^{-2}$ .
  - Stopped mounting for ~1 hour
  - Fully erasable and now normal

- **Micron 32-layer TLC**
  - $1 \times 10^8 \text{cm}^{-2}$  N (LET=1.4 MeVcm<sup>2</sup>/mg)

(01) Raw Read Error Rate	100	100	0	3677	ok
<b>(05) Reallocated Sector Count</b>	<b>4</b>	<b>4</b>	<b>10</b>	<b>1120</b>	<b>failed</b>
(09) Power On Hours Count	100	100	0	648	ok
(0C) Power Cycle Count	100	100	0	55	ok
(AB) Unknown Attribute	100	100	0	2	ok
(AC) Unknown Attribute	100	100	0	1087	ok
(AD) Unknown Attribute	100	100	0	4	ok
(AE) Unknown Attribute	100	100	0	38	ok
(B7) SATA Downshift Count	100	100	0	0	ok
(B8) End To End Error Detection	100	100	0	0	ok
(BB) Uncorrectable Error Count	100	100	0	27	ok
(C2) Temperature	77	41	0	253404184...	ok
(C4) Reallocated Event Count	100	100	0	1120	warning
(C5) Current Pending Sector	100	100	0	24	warning
(C6) Offline Uncorrectable	100	100	0	0	ok
(C7) Interface CRC Error Count	100	100	0	1	attention



# Challenges



- **SSD testing adds layers of abstraction and mapping on top of error-correcting code.**
- **Effectively impossible to see any individual errors, even MBUs and minor SEFIs; major SEFI events likely to dominate error-response**
- **Must test as a black-box system**
  - **Ok if you're trying to *characterize* a black-box system, but limited insight into marginal degradation at part level**



# Future Plans

- **Generational scaling in 3D layer count and feature size will continue**
  - Test piece parts when able, but SSD-type testing possible as well
- **Evaluate combined effects, particularly as TLC/QLC cells continue to erode margins and increase RBER**
  - TID/SEE/Endurance/Retention all tightly coupled